

Serial No.: 09/848,997  
Group Art Unit: 2822

**AMENDMENT**

**IN THE CLAIMS:**

- Please replace pending claim 7 with the following clean amended claims 7:

7. (Amended) A method for planarization of low dielectric constant ILD layers on a semiconductor wafer comprising:  
    providing an oven having a rotatable wafer holder provided therein;  
    placing the semiconductor wafer on the wafer holder;  
    rotating the wafer holder with the semiconductor wafer thereon;  
    spinning on the low dielectric constant ILD material on to the semiconductor wafer in the oven;  
    soft baking the low dielectric constant ILD material at a soft bake temperature in the oven;  
    holding the low dielectric constant ILD material at a temperature below the hard bake temperature in the oven;  
    applying mechanical pressure to the ILD layer on the semiconductor wafer using a mechanical device to apply rotating pressure to the ILD layer in the oven;  
    applying heat to the ILD layer on the semiconductor wafer through the mechanical device simultaneously with the applying the mechanical pressure in the oven;  
    hard baking the low dielectric constant ILD material at a hard bake temperature in the oven;  
    cooling the low dielectric constant ILD material in the oven; and  
    annealing the low dielectric constant ILD material in the oven.